

Please amend the subject application as follows:

**IN THE CLAIMS:**

Please accept amended claims 1-3, 6-8 and 16 as follows:

1. (currently amended) A silicon crystallization system comprising:

a plurality of beam generators each generating a laser beam, each laser beam having substantially the same intensity and a duration time;

a plurality of optical units controlling a ~~synthesized~~ beam, wherein the ~~synthesized beam with~~ has substantially the same intensity as the intensity of each of the laser beams, ~~is formed by synthesizing the laser beams from the beam generators with a time difference~~ and has substantially the same duration time as the sum of each duration time of the laser beams; and

a plurality of stages for mounting substrates provided with silicon layers to be polycrystallized by the output beams from the optical units.

2. (currently amended) The system of claim 1, wherein a duration of the ~~synthesized~~ beam is longer than each of the laser beams generated by the beam generators.

3. (currently amended) The system of claim 2, further comprising a beam synthesizer synthesizing the laser beams and generating the synthesized beam.

4. (original) The system of claim 1, further comprising a chamber provided with the optical unit and the stage therein.

5. (canceled)

6. (currently amended) A silicon crystallization system comprising:

a plurality of beam generators each generating a laser beam, each laser beam having substantially the same intensity and a duration time;

a beam splitter receiving and splitting a synthesized-beam into a plurality of beamlets, wherein the ~~synthesized-beam with~~ has substantially the same intensity as the intensity of each of the laser beams, ~~is formed by synthesizing the laser beams from the beam generators with a time difference~~ and has substantially the same duration time as the sum of each duration time of the laser beams;

a plurality of optical units controlling the beamlets from the beam splitter; and

a plurality of stages for mounting substrates provided with silicon layers to be polycrystallized by the beamlets from the optical units.

7. (currently amended) The system of claim 6, wherein a duration of the synthesized beam is longer than each of the laser beams generated by the beam generators.

8. (currently amended) The system of claim 6, further comprising a beam synthesizer synthesizing the laser beams and generating the synthesized-beam.

9. (original) The system of claim 6, further comprising a plurality of chambers, each chamber provided with one of the optical units and one of the stages therein.

10. (original) The system of claim 9, wherein one of the chambers loads a substrate while another of the chambers performs polycrystallization.

11. (original) The system of claim 9, wherein at least two of the chambers simultaneously performs polycrystallization.

12. (previously presented) The system of claim 10, wherein the polycrystallization comprises sequential lateral solidification (SLS).

13. (previously presented) The system of claim 10, wherein the number of the chambers is three.

14. (previously presented) The system of claim 10, wherein the chambers perform the polycrystallization in turn.

15. (canceled)

16. (currently amended) A silicon crystallization system comprising:

a plurality of beam generators each generating a laser beam, each laser beam having substantially the same intensity and a duration time;

a beam synthesizer generating a ~~synthesized beam with~~ wherein the beam ~~has~~ substantially the same intensity as the intensity of each of the laser beams from

the laser beams generated by the beam generators, and has substantially the same duration time as the sum of each duration time of the laser beams;

a beam splitter splitting the synthesized-beam into a plurality of beamlets; and

a plurality of chambers, each chamber including an optical unit controlling one of the beamlets from the beam splitter and a stage for mounting a substrate provided with a silicon layer to be polycrystallized by the beamlet from the optical unit.

17. (original) The system of claim 16, wherein one of the chambers loads a substrate while another of the chambers performs polycrystallization.

18. (original) The system of claim 16, wherein at least two of the chambers simultaneously perform polycrystallization.

19. (previously presented) The system of claim 17, wherein the polycrystallization comprises sequential lateral solidification (SLS).

20. (previously presented) The system of claim 17, wherein the chambers perform the polycrystallization in turn.

21.-27. (canceled)